

Schottky Barrier Rectifier

MBR6080PT

FEATURES

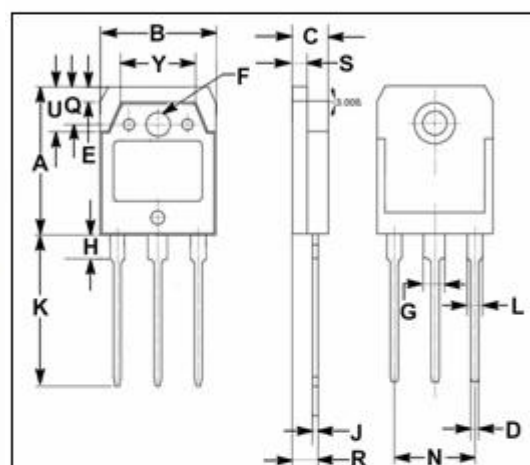
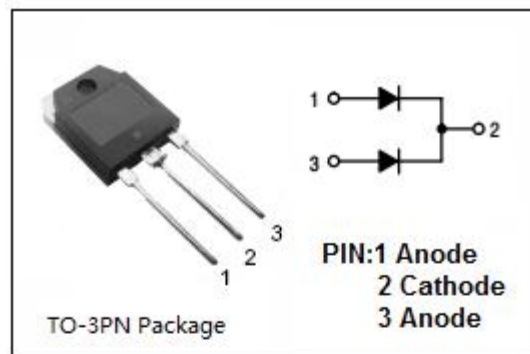
- Plastic material used carriers Unerwriter Laboratory
- Metal silicon rectifier, majonty carrier conduction
- Low Power Loss,High Efficiency
- Guard ring for transient protection
- High Surge Capability,High Current Capability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For use in low voltage ,high frequency inverters,free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{RRM} V _{RWM} V _R	Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	80	V
V _{R(RMS)}	RMS Reverse Voltag	56	V
I _{F(AV)}	Average Rectified Forward Current	40	A
I _{FSM}	Nonrepetitive Peak Surge Current 8.3ms single half sine-wave superimposed on rated load conditions	400	A
T _J	Junction Temperature	-65~150	°C
T _{stg}	Storage Temperature Range	-65~175	°C



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

Schottky Barrier Rectifier**MBR6080PT****THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.5	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 μ s, Duty Cycle $\leq$ 1%)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_F	Maximum Instantaneous Forward Voltage	$I_F = 30A$; $T_c = 25^{\circ}C$	0.8	V
I_R	Maximum Instantaneous Reverse Current	$V_R = V_{RWM}; T_c = 25^{\circ}C$	0.1	mA
		$V_R = V_{RWM}; T_c = 125^{\circ}C$	20	